

2N2219
2N2219A

SILICON
NPN TRANSISTORS



TO-39 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2219 and 2N2219A are silicon NPN transistors manufactured by the epitaxial planar process, and designed for small signal general purpose and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	2N2219	2N2219A	UNITS
Collector-Base Voltage	V_{CB0}	60	75	V
Collector-Emitter Voltage	V_{CEO}	30	40	V
Emitter-Base Voltage	V_{EBO}	5.0	6.0	V
Continuous Collector Current	I_C		800	mA
Power Dissipation	P_D		800	mW
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D		3.0	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	2N2219		2N2219A		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=50\text{V}$	-	10	-	-	nA
I_{CBO}	$V_{CB}=60\text{V}$	-	-	-	10	nA
I_{CEV}	$V_{CE}=60\text{V}, V_{EB}=3.0\text{V}$	-	-	-	10	nA
I_{EBO}	$V_{EB}=3.0\text{V}$	-	10	-	10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60	-	75	-	V
BV_{CEO}	$I_C=10\text{mA}$	30	-	40	-	V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0	-	6.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.4	-	0.3	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	1.6	-	1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	1.3	-	1.2	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	2.6	-	2.0	V
h_{FE}	$V_{CE}=10\text{V}, I_C=100\mu\text{A}$	35	-	35	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	50	-	50	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75	-	75	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	100	300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	50	-	50	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	30	-	-	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	-	-	40	-	

R1 (31-July 2013)

2N2219
2N2219A

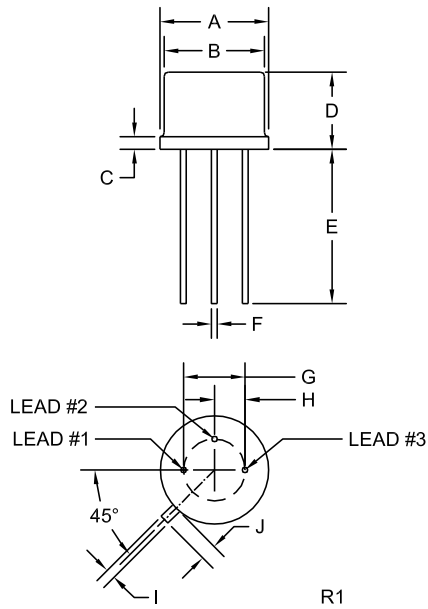
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	2N2219		2N2219A		UNITS
		MIN	MAX	MIN	MAX	
f_T	$V_{CE}=20\text{V}, I_C=20\text{mA}$	250	-	300	-	MHz
C_{ob}	$V_{CB}=10\text{V}, f=100\text{kHz}$	-	8.0	-	8.0	pF
t_{on}	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_B=15\text{mA}$	-	35	-	35	ns
t_{off}	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	285	-	285	ns

TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

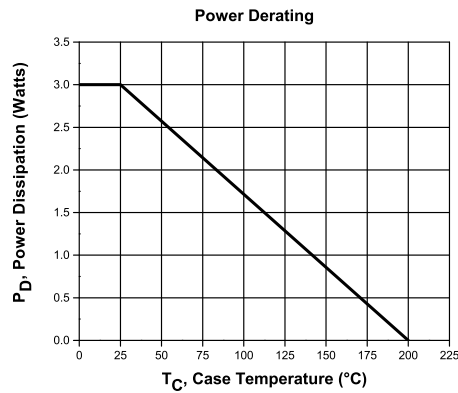
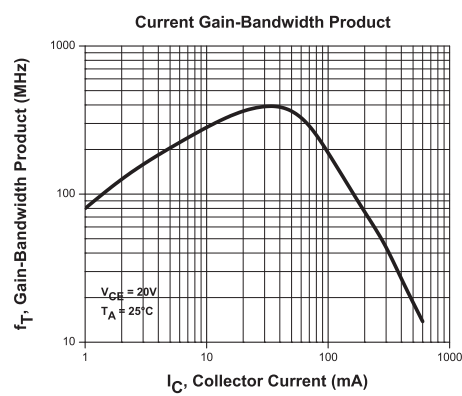
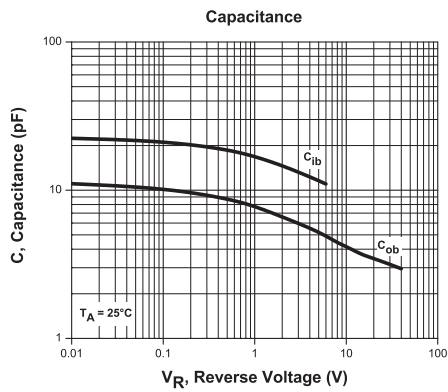
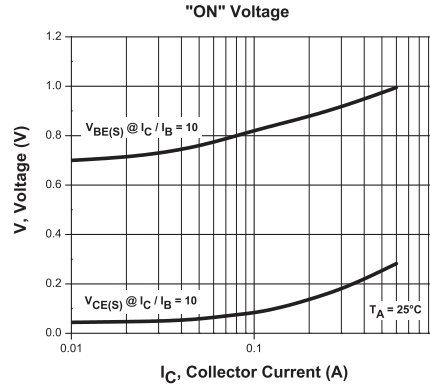
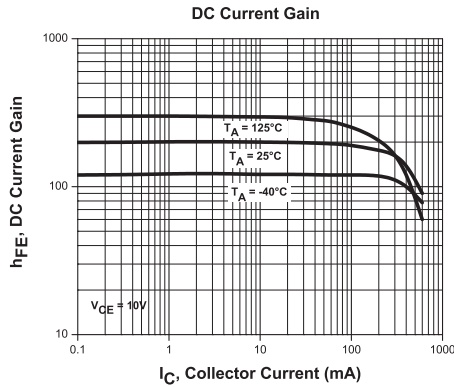
R1 (31-July 2013)

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TYPICAL ELECTRICAL CHARACTERISTICS



R1 (31-July 2013)